
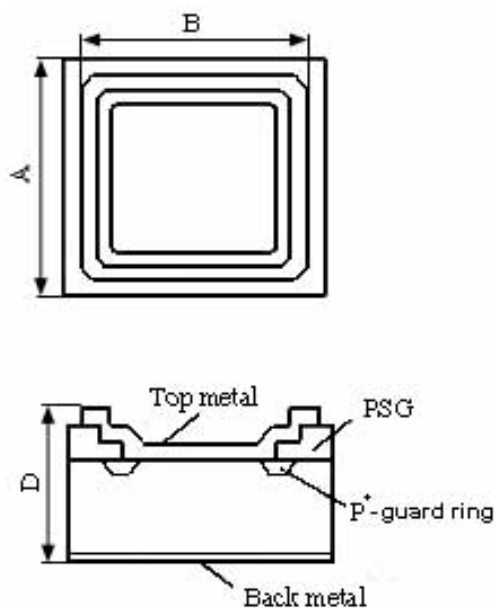


**SCHOTTKY DIODES KDS-05040I.**  
PRELIMINARY



Oct. 2013

 <b>VSP-MIKRON</b>	<b>5A/40V. Die Size-65mil.</b>			
<b>Electrical Characteristics</b>	<b>Symbol</b>	<b>Unit</b>	<b>Spec. limit</b>	<b>Die Sort</b>
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	5,0	-
DC Forward Voltage @ 25°C, $I_F=5,0A$	$V_F$	V	0,45	0,43
Maximum Reverse Current  @ 25°C, $V_R=45V$ 25°C, $V_R=40V$ 100°C, $V_R=40V$	$I_R$	mA	- 0,6 55,0	0,6 0,5 50,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	110	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<125°C$ .	$I_{RRM}$	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	125	



<b>DIM</b>	<b>ITEM</b>	<b>Mm</b>
Ax Ay	Wafer Form Die Size	1650 1650
Bx By	Top Metal Size	1470 1470
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.  
*Backside metal:* **Ti-Ni-Ag**.